



**COMPLEMENTARY SILICON POWER TRANSISTORS**

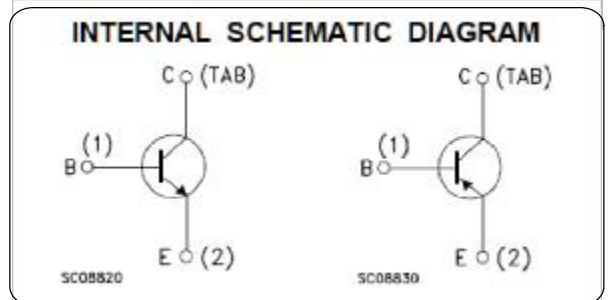
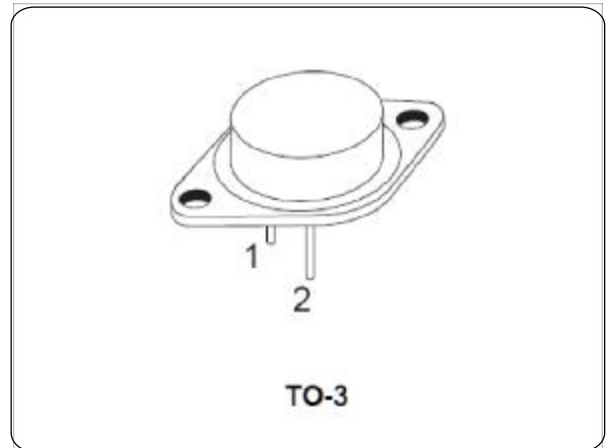
**2N3055/MJ2955**

**DESCRIPTION**

The 2N3055 is a silicon Epitaxial-Base Planar NPN transistor mounted in Jedec TO-3 metal case. It is intended for power switching circuits, series and shunt regulators, output stages and high fidelity amplifiers. The complementary PNP type is MJ2955.

**ABSOLUTE MAXIMUM RATINGS ( Ta = 25 °C)**

Parameter	I	Value	Unit
Collector-Base Voltage	$V_{CB0}$	100	V
Collector-Emitter Voltage	$V_{CEO}$	60	V
Emitter-Base Voltage	$V_{EBO}$	7	V
Collector Current	$I_C$	15	A
Base Current	$I_B$	7	A
Total Dissipation at	$P_{tot}$	115	W
Max. Operating Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	0	°C



**ELECTRICAL CHARACTERISTICS ( Ta = 25 °C)**

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector Cut-off Current	$I_{CEO}$	$V_{CE}=50V, I_B=0$	—	—	0.7	mA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=7V, I_C=0$	—	—	5.0	mA
Collector-Emitter Sustaining Voltage	$V_{CEO}$	$I_C=100mA, I_B=0$	60	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=4.0V, I_C=4.0A$	30	—	70	
	$h_{FE(2)}$	$V_{CE}=4.0V, I_C=10A$	15	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=4.0A, I_B=400mA$	—	—	1.0	V
		$I_C=10A, I_B=3.3A$	—	—	3.0	
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE}=4V, I_C=4.0A$	—	—	1.8	V
Current Gain Bandwidth Product	$f_T$	$V_{CE}=4.0V, I_C=500mA$	—	3.0	—	MHz